IGBT Modules and Applications (ZJU-FJU BDU SEMINAR)

2018 6 29 2 5
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14:00-14:10 Greeting, Introduction of Fuji Semiconductor Business,

Speaker: Naoto Fujishima, Fuji Electric Co., Ltd

14:10-14:40 High I2t capability power modules for x EV power train with leadframe and RC-IGBT combination,

Speaker: Akihiro Osawa, Fuji Electric Co., Ltd.

14:40-15:05 High power next Core(HPnC) package with 3.3kV SiC Hybrid chip combination,

Speaker: Yusuke Sekino, Fuji Electric Co., Ltd.

15:05-15:30 1,700V IGBT module with newly developed 7th Generation technology,

Speaker: Song Chen, Fuji Electric (China) Co., Ltd

15:30-15:40 Short Break

15:40-16:05 Influence of negative voltage between gate and emitter to the turn-off behavior of IGBT device,

Speaker: Fumio Yukawa, Fuji Electric Co., Ltd

16:05-16:30 Expansion of power rating with 7th-Generation “X Series” RC-IGBT Modules for Industrial Applications,

Speaker: Akio Yamano, Fuji Electric Co., Ltd

16:30-16:40 Q&A and Closing

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